

# SOT23 SILICON PLANAR DUAL SCHOTTKY BARRIER DIODES

**BAS70-04  
BAS70-05  
BAS70-06**

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			<p><b>SOT23</b></p>
<b>SERIES PAIR</b>	<b>COMMON CATHODE</b>	<b>COMMON ANODE</b>	
Device Type: BAS70-04	Device Type: BAS70-05	Device Type: BAS70-06	
Partmarking Detail: 2Z	Partmarking Detail: 2Z5	Partmarking Detail: 1Z	

## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}\text{C}$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltage	$V_{BR}$	70		V	$I_R=10\mu\text{A}$
Reverse Leakage Current	$I_R$		200	nA	$V_R=50\text{V}$
Forward Voltage	$V_F$		410	mV	$I_F=1\text{mA}$
Forward Current	$I_F$	15		mA	$V_F=1\text{V}$
Capacitance	$C_T$		2.0	pF	$f=1\text{MHz}, V_R=0$
Effective Minority Lifetime (1)	$\tau$		100	ps	$f=54\text{MHz}, I_{pk}=20\text{mA}$ (Krakauer Test Method)

(1) Sample Test

For typical characteristics graphs see ZC2800E datasheet.